



Curriculum Vitae

1. General Information:

(a) Name: Dr. Sheshmani K. Dubey

(b) Address : Department of Physics, University of Mumbai

E-Mail: skdubey@physics.mu.ac.in/skdubeymu@gmail.com

2. Academic Qualifications: *M. Sc.; Ph. D. University of Mumbai*

Academic Staff College Orientation / Refresher/ Short Term courses attended:

Sr.No.	Name of the Course	Place	Duration	Sponsoring Agency
1	Refresher Course	UGC-Academic Staff College, University of Mumbai	18 th February to 14 th March 1998	<u>UGC, New Delhi</u>
2	Refresher Course	UGC-Human Resource Development Centre, Amravati University, Amravati	10 th July to 29 th July 2017	<u>UGC, New Delhi</u>
3	Refresher Course	UGC-Human Resource Development Centre, Kumau University, Nanital	04 th October 2017 to 28 th October 2017	<u>UGC, New Delhi</u>
4	Teachers Training Regional Workshop for International Day of Yoga	University of Mumbai, Kaivalyadhama & Ministry of Ayush	23 rd May to 29 th May 2016	Ministry of Ayush, Government of INDIA
5	Certificate Course in Vacuum Science, Techniques and Applications	Mumbai University & Indian Vacuum Society	5 th December to 17 th December 1998	Indian Vacuum Society

3. Title of the Ph. D. Thesis:

“Studies of Al₂O₃.SiO₂ Composite Oxide Layers Synthesized by Ion Implantation”

4. Area of Specialization:

- Ion implantation,
- Swift heavy ion irradiation,
- Dilute Magnetic Semiconductors
- Thin Films
- VLSI Design and Circuits
- Research Guide: 1st July 2003

5. Research Degree Awarded Under My Supervision:

Ph. D -15, M. Phil-01, M. Sc (By Research)-01

6. Research Project Carried Out:

(i) As Principal Investigator:

<u>Sr.No.</u>	<u>Title of the Project</u>	<u>Funding Agency</u>	<u>Duration</u>	<u>Budget</u>	<u>Remarks</u>
1.	Study of defects in high energy ^{56}Fe implanted silicon	NSC / UGC New Delhi	Three years (1999-2002)	Rs.2,92,000/	Completed Successfully
2.	Development of the vacuum annealing system for the study of ion implanted samples.	University of Mumbai	One years (2000 - 2001)	Rs. 60,000/	Completed Successfully
3.	Ion implantation study of GaSb grown by Czochralsky Technique.	University. of Mumbai	One year (2001-2002)	Rs. 40,000/-	Completed Successfully
4.	High Energy ion irradiation of InP and GaP semiconductors.	NSC/ UGC New Delhi	Three Years (2004 –2007)	Rs.3,75,000/	Completed Successfully
5.	Studies on the iron based nanoclusters in Si and GaAs semiconductors synthesized by ion implantation	UGC-DAE consortium, Mumbai	Three Years (2006 –2009)	Rs.1,05,000/	Completed Successfully
6.	Studies of dilute magnetic Semiconductors (DMS's) formed by ion implantation and pulsed laser melting.	DST, New Delhi	Three years 2007-2010	Rs. 8,76,000/-	Completed Successfully
7.	Study the effects of high energy irradiation in III-V compound (GaP and InP) semiconductors by ^{107}Ag ions	UGC-IUA C New Delhi	Three Years 2010 -2012	Rs.7.26 Lakh	Completed Successfully
8.	Study the effects of silicon		Year 2016-		

	negative ion implantation in GaAs using LEIBF”	UGC IUAC New Delhi	19		Rs TA/DA	
9.	Fabrication and swift heavy ion engineering of Ga ₂ O ₃ based new generation devices for high power applications	SERB-NDPF, DST, New Delhi	Year 2016-2018		19.20 L	-----

(ii) As Co-Investigator:

9.	Growth and Ion-Implantation doping of Indium Antimonide”	University of Mumbai	1999-2000,		Rs. 35,000/-	Successfully completed
10.	“Structural and Electrical Studies on Ion-Implantation Synthesis of Insulating Layers on Silicon	U.G.C. New Delhi	Three Years 2001-2004		Rs.6.77 Lakhs	Successfully completed
11.	Ion- Beam Synthesis of Buried Insulating Layers in Silicon for Semiconductor devices	UGC-DAE CSR (IUC-DAEF)/KC	Three Years 2004 to 2007)		Rs.3.45 Lakh	Successfully completed
12.	ERDA studies of ion-beam synthesized surface / buried silicon oxynitride layers and swift heavy ion induced recrystallization of SOI structures	NSC-UGC, New Delhi	Three Years 2004 to 2007)		Rs. 3.45 Lakh	Successfully completed
13.	Fe and N diffusion mechanism in FeN using neutron reflectivity	UGC-DAE CSR , Mumbai	2008 -2010		Rs. 3.21Lakh	Successfully completed

(iii) Participated in Departmental Research Projects

14.	Development of device –grade nano materials using ion beam	DST, New Delhi			Rs. 63 Lakh	
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15.	SAP (Level -I), UGC	UGC, New Delhi	Rs. 33 Lakh
16.	FIST (Level-1) DST	DST, New Delhi	41.50 Lakh
17.	SAP (Level -II), UGC	UGC, New Delhi	Rs. 44 lakhs
18.	FIST (Level-II) DST	DST, New Delhi	99 Lakh

7. Seminars, Conferences, Symposia, Workshops etc. Orgainezed:

Sr. No.	Name	Duration	Place
1	Nanotechnology and Ion Beams'	21 –22 March 2005	Department of Physics, University of Mumbai, Mumbai
2.	National Workshop on Nanostructured Materials for Energy Devices and Environment	17-18 August 2011	Department of Physics, University of Mumbai, Mumbai
3.	National Workshop on Python in Science Education	19-20 September, 2013	Department of Physics, University of Mumbai, Mumbai
4.	National Workshop on Particle Accelerators: Science, Technology and Applications,	29 th November, 2014	Department of Physics, University of Mumbai, Mumbai

8. Research Papers Published:

I have more than 150 Research Publications in many reputed journals / symposia/ conferences/ workshop etc in the field ion implantation;

Sr. NO International / National Journals / Edited in Volum

- 1 Electrical resistivity and C-V Characteristics of Al₂O₃-SiO₂ composite layers prepared by Oxygen ion implantation; S.K. Dubey and A.D. Yadav; *Bull. I.V.S, Vac. News* 20(1) (1989) pp. 9-12.
- 2 Electrical conduction in Al₂O₃-SiO₂ double dielectric layers synthesized by ion implantation; S.K.Dubey and A.D.Yadav; *Indian J.Phys.* 65A (5) (1991) pp. 434 – 440.
- 3 Rutherford backscattering study of oxygen ion-implanted aluminum thin films on silicon; S.K.Dubey and A.D.Yadav; *Indian J.Phys.* 65A (5) (1991) pp. 428-433.

- 4 Study of diffusion in aluminum-silicon system by X-ray photoelectron spectroscopy; S.K.Dubey and A.D.Yadav and P.M.Raole; *Bull. I.V.S. Vac. News* 22 (1)(1991) pp21-24.
- 5 XPS depth profile of Ion-Beam synthesized Al₂O₃-SiO₂ composite oxide layers on silicon".S.K. Dubey, A.D. Yadav, P.M. Raole and P.D. Prabhawalkar, *International Society for Optical Engineering (USA), Tata Mc Graw Hill Publication Company LTD. New Delhi. Vol. 1523 (1992), pp. 314-317*
- 6 XRD, ESCA and C-V investigations of Al₂O₃-SiO₂ composite thin films synthesized by high dose oxygen ion implantation; S.K.Dubey and A.D.Yadav, *Nucl. Instr. and Meth. in Physics Research B* 143 (4) (1998) 493-498.
- 7 Structural and Electrical properties of high dose nitrogen implanted tantalum; A.D.Yadav, S.K. Dubey, G.K.Gupta and T.K. Gundu Rao, *Radiation effects and defects in solids*, 153, (2000) 25-33.
- 8 Structural studies of 20 KeV oxygen implanted silicon. G.K. Gupta, A.D. Yadav, T.K. Gundu Rao and S. K. Dubey; *Nucl. Instr. and Meth. in Physics Research B* 168 (4) (2000) pp.503-509.
- 9 Electrical characteristics of low energy tellurium implanted indium antimonide; A.D.Yadav , Bhagyashree Rao, S.K. Dubey and B.D. Gadkari; *Material Science and Engineering B-84 (2001) 176*.
- 10 Investigation of 70 MeV iron irradiation induced defects in c-silicon; Bhagyashree A.K., S.K. Dubey, A.D.Yadav, K.G. Bhole, Tanuja Mohanti and D. Kanjilal, *Nuclear Instruments and Methods in Physics Research B* 211 (2003) 383-388
- 11 High Energy ion implantation of iron in silicon; K.G. Bhole, Bhagyashree A.K., S.K. Dubey, A.D.Yadav, Tanuja Mohanti and D. Kanjilal; *Nuclear Instruments and Methods in Physics Research B* 212 (2003) 525-529.
- 12 Synthesis of silicon oxynitride layers by dual ion-implantation and their annealing behavior"; Alka R Chauhan, Geeta Bhatt, A.D. Yadav and S.K.Dubey; *Nuclear Instruments and Methods in Physics Research B* 212 (2003) 451- 457
- 13 Investigation of defects in reactive ion implantation silicon; Geeta Bhatt, A.D. Yadav, S.K.Dubey and T.K. Gundu Rao; *Nuclear Instruments and Methods in Physics Research B* 222 (2004) 75-80 .
- 14 Distribution of radiation induced defects and modification of optical constants of GaAs implanted with high energy ⁵⁶Fe ions, M.M. Belekar, A.M. Narsale, B.M.Arora, K. V. Sukhatankar, S.K. Dubey and V.P. Salvi, *Nuclear Instruments and Methods in Physics Research –B* 226, pp 301-308 (2004).
- 15 Studies of defects and annealing behavior of silicon irradiated with 70 MeV ⁵⁶Fe ions, S.K.Dubey, A.D.Yadav, B. A. Kamalapurkar, M. Gokhale, T. Mohanty, and D.Kanjilal, *Nuclear Instruments and Methods in Physics Research B* 244 (2006) 157-160.
- 16 Study of optical properties of swift heavy ion irradiated gallium antimonide; S.K. Dubey, R.L. Dubey, A.D. Yadav, V. Jadhav T.K. Gundu Rao, T.Mohanty and D. Kanjilal; *Nuclear Instruments and Methods in Physics Research B* 244 (2006) 141-144
- 17 Synthesis of buried silicon oxynitride layers by ion implantation for Silicon – on insulator (SOI) structures, A.D. Yadav , Rucha H. Polji, Vibha Singh, S.K.Dubey and T.K. Gundu Rao; *Nuclear Instruments and Methods in Physics Research B* 245(2006) 475-479.
- 18 Investigations on the effect of argon ion bombardment on the structural and optical properties of crystalline gallium antimonide, S.D. Pandey, S.K. Dubey, R. L. Dubey, A.D. Yadav, S.J. Gupta and

B.M. Arora, *Radiation Effects and Defects in Solids*, 161 (2006) 433.

- 19 Investigation of nano size defects in InP induced by Swift iron ions, R.L. Dubey, S.K. Dubey, A.D. Yadav, S.J. Gupta, T.K. Gundu Rao, T. Mohanty and D. Kanjilal, *Nuclear Instruments and Methods in Physics Research B* 257/1-2; (2007) 287-292.
- 20 Study of structure and Electrical characteristics of silicon oxynitride layers synthesized by dual ion implantation in silicon and their annealing behaviour, A.D. Yadav, Geeta Bhatt and S.K. Dubey, *ECS Transactions* 8(1) (2007) 117-123.
- 21 FTIR and RBS studies of Ion –Beam synthesized buried silicon oxide layers; A.P. Patel, A.D. Yadav, S.K. Dubey, B.K. Panigrahi and K.G. M. Nair, *Nuclear Instruments and Methods in Physics Research B* 266 (2008)1443-1445.
- 22 Structural characterization of buried nitride layers formed by nitrogen ion implantation; A. D. Yadav, A.P. Patel, S.K. Dubey, B.K. Panigrahi, R. Kesavamoorthi and K.G. M. Nair; *Nuclear Instruments and Methods in Physics Research B* 266 (2008)1447-1449.
- 23 Structural studies of silicon oxynitride layers formed by low energy ion implantation; A.R. Chauhan, A.D. Yadav, S.K. Dubey and T.K. Gundu Rao, *Nuclear Instruments and Methods in Physics Research B* 266 (2008) 1537-1541.
- 24 Specific Features of Steady –State implantation of Crystalline Silicon with Molecular oxygen – Nitrogen beam: Si L_{2,3} X-ray emission spectra; D.A. Zatsepin, L.A. Shein, E.Z. Kurmaev, V.M. Cherkashenko, S.N. Shamin, N.A. Shamin, N.A. Skorikov, A.D. Yadav and S.K. Dubey; *Physics of Solid State*, 50 -1(2008) PP 146-151.
- 25 Study of swift (100 MeV) Fe⁹⁺ ion irradiated gallium antimonide, Vidya Jadhav, S.K. Dubey, R.L. Dubey, S. Tripathi, A.D. Yadav, S.J. Gupta, T.K. Gundu Rao and D. Kanjilal, *Nuclear Instruments and Methods in Physics Research B* 266 (2008)1443-1445.
- 26 Investigation of structure and composition of buried oxide layers formed by oxygen ion implantation into silicon, A. Patel, A.D. Yadav, S.K. Dubey, Panigrahi, KGM Nair; *Radiation Effects and Defects in Solids*, Vol. No. 164(2009) 49-58
- 27 Study of SHI induced recrystallization effects in SOI structures synthesized by nitrogen and oxygen ion implantation in silicon; A.D. Yadav, Rucha H. Polji, S.K. Dubey, Saif A Khan and D.K. Avasthi, *Vacuum* 83(2009) 889-8891.
- 28 Studies of swift iron ions in crystalline silicon, N.K. Kachhap, S.K. Dubey, R.L. dubey, A.D. Yadav, D. Kanjilal and S.K. Deshpande, *Surface Coating and Technology* 203(2009)2422-2426.
- 29 Effect of swift heavy ion (SHI) irradiation on nitrogen ion implanted silicon; A.P. Patel, A.D. Yadav, S.K. Dubey, B.K. Panigrahi, K.G.M. Nair, P. Kumar, D.Kanjilal, S.A. Khan and D.K. Awasthi; *Surface Coating and Technology* 203 (2009) 2651-2653.
- 30 Study of structure and surface modification of silicon on insulator (SOI) devices synthesized by dual ion implantation; Rucha H. Polji, A.D. Yadav, S.K. Dubey, P. Kumar and D. Kanjilal; *Surface Coating and Technology* 203(2009) 2654-2657
- 31 Effects of the swift iron ions in indium phosphide, R.L. Dubey, S.K. Dubey, A.D. Yadav and D.Kanjilal, *Surface Coating and Technology* 203 (2009) 2637-2641.
- 32 Structural and optical studies of GaSb implanted with iron ions, V.Jadhav, S.K. Dubey, R.L. Dubey, A.D. Yadav and D. Kanjilal, *Surface Coating and Technology* 203 (2009) 2670-2673.
- 33 Hi-ERDA, Micro-Raman and HRXRD studies of buried silicon oxynitride layers synthesized by dual ion implantation, Rucha H. Polji, A.D. Yadav, S.K. Dubey, Saif A Khan and D.K. Avasthi, *Vacuum*

83 (2009)1164-1168.

- 34 Studies on structure and electrical characteristics of oxide layers synthesized by reactive ion implantation into tantalum, V. Singh, A.D. Yadav, S.K. Dubey, P. Kumar, D. Kanjilal, *Surface Coating and Technology* 203 (2009) 2632-2636
- 35 Structural and optical properties of (Ga, Mn)As structure prepared by Ar²⁺ ion implantation S. Tripathi, R. L. Dubey, S. K. Dubey, A. D Yadav, P. Kumar⁺ and D. Kanjilal *American Institute of Physics (AIP)* 1313 (2010) 100-103.
- 36 ZFC and FC studies of gallium nitride implanted with Mn ions; N. S. Pradhan, S. K. Dubey[†], A. D Yadav B.K. Panigrahi, K.G.M. Nair and G. Jngam. *American Institute of Physics (AIP)* 1313 (2010) 159-161.
- 37 Structural, Compositional and Electrical Characterization of buried silicon oxide insulating layers synthesized by SIMOX process”, A. P. Patel, A. D. Yadav, S. K. Dubey, B. K. Panigrahi, K.G. M. Nair and P. Kumar, *American Institute of Physics (AIP) Proc, CP1249* (2010), pp.206-210.
- 38 Micro- Raman and UV-VIS studies of 100 MeV Ni⁴⁺ irradiated Cadmium Telluride thin films” Neelam Pahwa, A.D. Yadav, S.K. Dubey, A. P. Patel. *J. Nano- Electron. Phys.* 3, No.1, 414 (2011).
- 39 Effects of annealing on the structural and surface properties of buried silicon oxide layers synthesized by SIMOX process”; A. P. Patel, A. D. Yadav, S. K. Dubey, B. K. Panigrahi, K.G. M. Nair and D.C. Kothari, *Radiation Effects and Defects in Solids Vol. 166, No. 8-9, (2011)* 734.
- 40 Swift heavy ion induced nanostructures on the surface of GaP, R.L. Dubey, S.K. Dubey, A.D. Yadav and D. Kanjilal. *International Journal of Nanoscience* 10, no. 1(2011)105-109.
- 41 Raman scattering and FTIR studies of 100 MeV Fe⁹⁺ ion irradiated gallium phosphide. R.L. Dubey, S.K. Dubey, A.D. Yadav, Indra Sulania and D. Kanjilal; *Radiation Effects and Defects in Solids* 166 (2011) 743-748.
- 42 Magnetic and optical properties of Mn⁺ implanted gallium nitride and their effects on Si ion irradiation. N. Pradhan, S. K. Dubey[†], A. D Yadav[†]. *American Institute of Physics* 1349 (2011) 248-251.
- 43 Formation of (Ga,Mn)N dilute magnetic semiconductor by manganese ion implantation’, N.S. Pradhan, S.K. Dubey, A. D.Yadav, B.K. Panigrahi, K.G.M. Nair, Arvind Singh and D.C Kothari, *International Journal of Engineering and Physical Sciences* 6(2012)11.
- 44 Swift iron ion irradiation induced disorder in crystalline silicon”, N.K. Kachhap; R.L., Dubey, S.K. Dubey and D. Kanjilal; *Journal of Materials Science and Engineering B* 3 (1) (2013) 13-18.
- 45 Surface modification of indium phosphide by 100 MeV iron ions; R.L. Dubey, S.K. Dubey, A.D. Yadav and D. Kanjilal; *Radiation Effects and Defects*; Vol. 168, Nos. 7–8, 557–563, (2013)
- 46 Effects of 200 MeV silver ion irradiation on the optical properties of gallium phosphide; Vidya Jadhav, M. D. Kirkire, S. K. Dubey, A. D.Yadav, F. Singh and D. Kanjilal; *Radiation Effects and Defects* Vol.168, Nos.7–8, 564–570, (2013)
- 47 Synthesis of Nanocrystalline Thin Films of Gold on the Surface of GaSb by Swift Heavy Ion ; Vidya Jadhav, S. K. Dubey, A. D. Yadav and A. Singh, *American Institute of Physics* 1512 (2013) 1026-1027.
- 48 Annealing Behaviour of cadmium ion implanted GaSb; S.D. Pandey and S.K. Dubey; *proc. American Institute of Physics* 1512 (2013) 1034-1035.
- 49 Design and Simulation of FPGA based Digital System for Peak Detection and Counting; Amitkumar

- Singh, S.K. Dubey M.G. Bhatia; *International Journal of Advanced Research in Computer Science and Software Engineering Volume 3, Issue 11, November 2013 ISSN: 2277 128X*;
- 50 Design and Simulation of FPGAs Based Digital Discriminator: Amitkumar Singh, S.K. Dubey M.G. Bhatia; *International Journal of Advanced Research in Computer Science and Software Engineering; Volume 4, Issue 2,(2014) pp1134-1138.*
- 51 Structural and Optical Properties Studies of Mn⁺ ion implanted GaAs; Sharad Tripathi S. K. Dubey; V. S. Upadhyaya; *International Journal of Chemical and Physical Sciences. 3(2014)161.*
- 52 XRD and FTIR studies of argon ion implantation into manganese deposited gallium antimonide thin films; N.S. Pradhan and S. K. Dubey; *International Journal of Pure and applied research in engineering and Technology; 2(9) (2014) 118-126.*
- 53 Design and Simulation of Fpgas Based Digital Multi Channel Analyzer for Nuclear Spectroscopy Application Amitkumar Singh, S.K. Dubey and M.G. Bhatia ; *International Journal of Advanced Research in Computer Science and Software Engineering; Volume 4, Issue 8, (2014) 717.*
- 54 Review of Pulse Processing in Nuclear Physics; Amitkumar Singh, S.K. Dubey and M.G. Bhatia; *International Journal of Advanced Research in Computer Science and Software Engineering; Volume 4, Issue 8, August (2014) 550. ISSN: 2277 128X*
- 55 Structural and Optical Properties Studies of Mn⁺ Ion Implanted GaAs; S Tripathi, S.K. Dubey,V.S. Upadhyay; *International Journal of Chemical and Physical Sciences., Vol. 3 Special Issue – NCRTSM, April-2014. ISSN: 2319-6602.*
- 56 RBS and UV-VIS-NIR studies of low energy Mn⁺ ion implanted in GaAs substrate
S Tripathi, S.K. Dubey, V.S. Upadhyay; *International Journal of Chemical and Physical Sciences (IJCPS) 3 (4) (2014) ISSN:2319-6602.*
- 57 Structural, Optical and Morphological Properties of PVA/ Fe₂O₃ Nanocomposite Thin Films; V.S. Upadhyay, S.K. Dubey, A. Singhand S Tripathi; *International Journal of Chemical and Physical Sciences; (IJCPS) 3 (4) (2014) 44, ISSN:2319-6602.*
- 58 Micro Raman Scattering and GA-XRD studies of swift heavy (200 MeV) silver ion irradiated Gallium phosphide; M.D. Kirkire and S. K. Dubey; *International Journal of Science Research: 4-8 (2015) 711-712.*
- 59 Effects of argon ions irradiation on manganese metal deposited gallium antimonide thin films” Nana Pradhan and S. K. Dubey; *Journal of Advanced Science Letter 22, 849-853 (2016)*
- 60 Effects of passage of 200 MeV Ag⁹⁺ ions in indium phosphide at different depths; M.D. Kirkire, S.K. Dubey, Vidya Jadhav, A.D. Yadav, F. Singh & D. Kanjilal; *Radiation Effects & Defects in Solids, Vol. 170, Nos. 7–8 (2015), 690.*
- 61 Structural and optical studies of 100 MeV Ni⁷⁺ irradiated cadmium selenide thin films; R. Singh, A.D. Yadav Vidya Jadhav and S.K. Dubey; *Journal of Nano-and Electronic Physics 7(3) (2015) 03002.*
- 62 Study on Raman LO Phonon Signal of GaAs Implanted by Mn ions Sharad Tripathi, S. K. Dubey and B. K. Panigrahi; *Nuclear Instrumentation and Methods in physics Research B*
- 66 Optical properties and surface damage studies of crystalline silicon caused by swift iron ions;S. K. Dubey; *Nuclear Instrumentation and Methods in physics Research B 375 (2016) 67–70.*
- 68 Optical and structural properties of 100 MeV Fe⁹⁺ ion irradiated InP
R. L. Dubey, S. K. Dubey, S. P. Bodhane, and D. Kanjilal, AIP Conference Proceedings 1728, 020666 (2016);

- 69 Surface Modification and Irradiation Strength of InP and GaP; R. L. DUBEY and S. K. DUBEY. *International Journal of Chemical and Physical Sciences (IJCPS) Vol. 5, No.-2, Mar-Apr 2016 pp 51-58; ISSN:2319-6602*
- 71 Comparative study of nanoparticles doped in Liquid Crystal Polymer System; Krishnakant G. Mishra, S.K. Dubey, Santosh A. Mani, Madhavi S. Pradhan; *Journal of Molecular Liquids* 224 (2016) 668–671
- 72 Surface modification of gallium phosphide caused by swift (200 MeV) silver ions, S. K. Dubey; *Nuclear Instruments and Methods in Physics Research B* 392 (2017) 46–50
- 73 Effect of silicon negative ion implantation in semi insulating gallium arsenide, Ajay Yada, S. K. Dubey, R.L.Dubey, Vidya Jadhav, Vaishali Bambole, I. Sulania, D. Devrani and D. Kanjilal; Submitted to *Nuclear Instruments and Methods in Physics Research B* (2018)
- 74 XPS and SEM Analysis of GaAs Implanted with Silicon Negative Ions; Ajay Yadav, S.K.Dubey, R.L.Dubey, V.Bambole, V. Jadhav, N.B.V.Subramanyam, I. Sulania; Submitted to *Radiation Effects and Defects in Solids* (2018)
- 75 Effect of silicon negative ion implantation in SiO₂; Vishwakarma, S.K Dubey, R.L Dubey, A.Yadav, V. Jadhav, V. Bambole, I. Sulania, F. Singh, P.K. Kulariya, D. Kanjilal; Submitted to *Materials and Materials Transactions* (2018)

Edited in Volumes / Proceedings

Sr.No.

- 78 Study of oxide charge and interface state in Ion-Beam synthesized Al₂O₃-SiO₂ MOS structure; S.K.Dubey and A.D.Yadav; *Proc.Solid State Phys. (India)* 33C (1990) 421.
- 79 Al₂O₃-SiO_x composite oxide layer synthesis by Ion implantation; S.K.Dubey and A.D.Yadav; *Proc.Solid State Phys. (India)* 34C (1991) 459.
- 80** XPS depth profile of Ion-Beam synthesized Al₂O₃-SiO₂ composite oxide layers on silicon".S.K. Dubey, A.D. Yadav, P.M. Raole and P.D. Prabhawalkar, *International Society for Optical Engineering (USA), Tata Mc Graw Hill Publication Company LTD. New Delhi. Vol. 1523 (1992), pp. 314-317*
- 81 Structural Properties of Oxygen Implanted Al-Si, S.K.Dubey and A.D.Yadav; *Proc.Solid State Phys. (India)* 36C (1993) p 549.
- 82 C-V Studies of MOS Devices Prepared by Oxygen Ion-Implantation; A.D.Yadav, S.K.Dubey and G.K.Gupta; *Proc.Solid State Physics (India), Vol. 38C (1995), P. 464.*
- 83 FTIR study of silicon oxide synthesis by Ion-implantation; S.K.Dubey, A.D.Yadav, G.K.Gupta and T.K.Gundu Rao, *Proc. Solid State Phys. (India)* 39C(1996) 171.
- 84 Study of electron spin resonance of low energy oxygen implanted silicon; G.K.Gupta, A.D.Yadav, T.K.Gundu Rao and S.K.Dubey, *Proc.Solid State Phys. (India)* 40 C (1997) 248.
- 85 FTIR study of carbon implanted silicon by Sanjivani Desai, A.D.Yadav, G.K.Gupta, S.K.Dubey, T.K.Gundu Rao, *Proc.Solid State Phys. (India)* 40C (1997) 186.
- 86 Characterisation of tellurium implanted InSb crystal, Bhagyshree V.Rao, A.D.Yadav, S.K.Dubey, G.K.Gupta, D.B.Gadkari, A.P.Shah and B.M.Arora, *Proc.Solid State Phys (India)* 40C(1997) 462, India.

- 87 FTIR, ESR and C-V studies of 20 keV nitrogen implanted silicon; G.K. Gupta, A.D. Yadav, S. K. Dubey and T.K. Gundu Rao. *Proc.Solid State Phys.(India) 41C (1998) 479-480.*
- 88 Formation of P-N junction in InSb by ion – implantation; Bhagyashree V Rao, A.D.Yadav, S.K. Dubey, G.K. Gupta and D.B. Gadhkari, *Proc.Solid State Phys. (India) 41(1998) 510-511.*
- 89 Spectroscopic Ellipsometry of carbon ion implanted silicon; S. Desai, D. Bhattacharyya, A.D. Yadav and S.K. Dubey, *Proc.Solid State Phys. (India) 41C (1998) 291-292.*
- 90 C-V Investigation of $\text{Si}_x\text{O}_y\text{N}_z$ -Si Structure Synthesized by implantation; G .K.GUPTA, A.D. Yadav and S.K. Dubey; *Proc.Solid State Physics (India) 42C (1999).*
- 91 FTIR and XRD studies of InSb and $\text{In}_x\text{Ga}_{1-x}\text{Sb}$ single Crystal grown by Vertical Directional Solidification Technique; T.K.Achal, S.K.Dubey, P.Shashidharan and D.B. Ghadhkari; *Proc.Solid State Physics (India) 43 (2000) 534.*
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